

DC Input, High Voltage Photo Darlington Transistor Coupler

Description

The SLM352 series combine an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar high voltage darlington phototransistor detector in a plastic SOP4 package.

With the robust coplanar double mold structure, SLM352 series provide the most stable isolation feature.

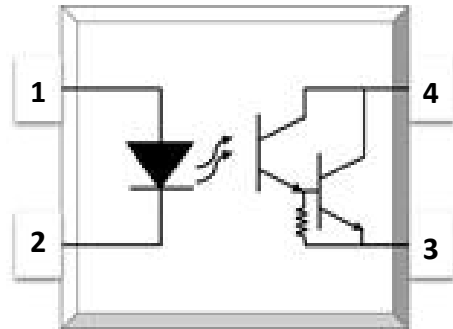
Features

- High isolation 3750 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Operating temperature range - 55 °C to 100 °C
- REACH compliance
- Halogen free
- MSL class 1
- Regulatory Approvals
 - UL - UL1577
 - VDE - EN60747-5-5(VDE0884-5)
 - CQC - GB4943.1, GB8898
 - cUL- CSA Component Acceptance Service Notice No. 5A

Applications

- Sequence controller
- Telephone/FAX
- System appliances, measuring instrument
- Programmable logic controller

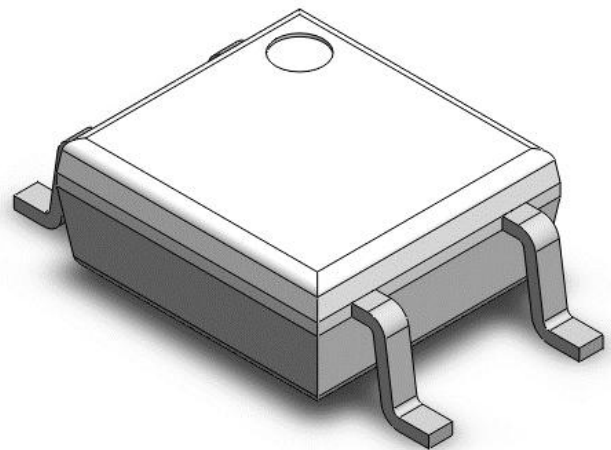
SCHEMATIC



PIN DEFINITION

1. Anode
2. Cathode
3. Emitter
4. Collector

PACKAGE OUTLINE



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT	NOTE
INPUT				
Forward Current	I_F	60	mA	
Peak Forward Current	I_{FP}	1	A	1
Reverse Voltage	V_R	6	V	
Input Power Dissipation	P_I	100	mW	
OUTPUT				
Collector - Emitter Voltage	V_{CEO}	350	V	
Emitter - Collector Voltage	V_{ECO}	0.1	V	
Collector Current	I_C	150	mA	
Output Power Dissipation	P_O	150	mW	
COMMON				
Total Power Dissipation	P_{tot}	200	mW	
Isolation Voltage	V_{iso}	3750	V _{rms}	2
Operating Temperature	T_{opr}	-55~110	°C	
Storage Temperature	T_{stg}	-55~125	°C	
Soldering Temperature	T_{sol}	260	°C	

Note 1. 100 μ s pulse, 100Hz frequency

Note 2. AC For 1 Minute, R.H. = 40 ~ 60%

ELECTRICAL OPTICAL CHARACTERISTICS at Ta=25°C							
PARAMETER	SYMBOL	MIN	TYP.	MAX.	UNIT	TEST CONDITION	NOTE
INPUT							
Forward Voltage	V _F	-	1.24	1.4	V	IF=10mA	
Reverse Current	I _R	-	-	10	μA	VR=6V	
Input Capacitance	C _{in}	-	10	-	pF	V=0, f=1kHz	
OUTPUT							
Collector Dark Current	I _{CEO}	-	-	200	nA	VCE=200V, IF=0	
Collector-Emitter Breakdown Voltage	BV _{CEO}	350	-	-	V	IC=0.1mA, IF=0	
Emitter-Collector Breakdown Voltage	BV _{ECO}	0.1	-	-	V	IE=0.1mA, IF=0	
TRANSFER CHARACTERISTICS							
Current Transfer Ratio	CTR	1000	-	15000	%	IF=1mA, VCE=2V	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	-	1.2	V	IF=20mA, IC=100mA	
Isolation Resistance	R _{ISO}	10 ¹²	10 ¹⁴	-	Ω	DC500V, 40 ~ 60% R.H.	
Floating Capacitance	C _{IO}	-	0.6	1	pF	V=0, f=1MHz	
Cut-off Frequency	f _c	-	6	-	kHz	VCE=2V, IC=2mA RL=100Ω, -3dB	3
Response Time (Rise)	t _r	-	91.5	300	μs	VCE=2V, IC=20mA RL=100Ω	4
Response Time (Fall)	t _f	-	21.4	100	μs		4

Note 3. Fig.12&13

Note 4. Fig.14

CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

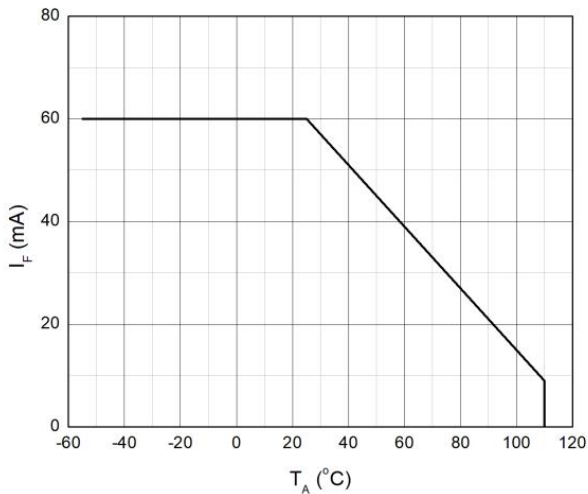


Fig.2 Collector Power Dissipation vs. Ambient Temperature

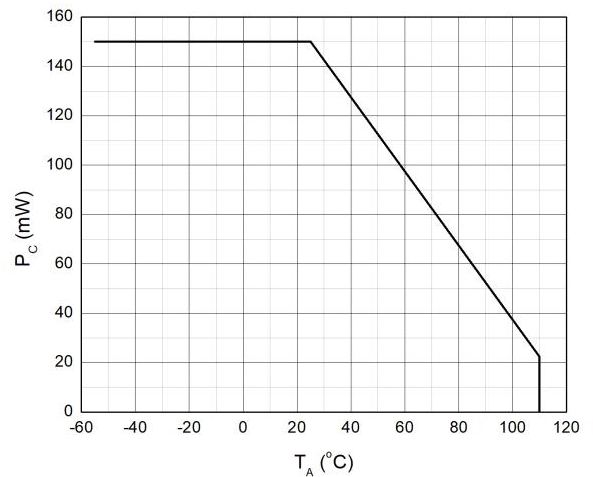


Fig.3 Forward Current vs. Forward Voltage

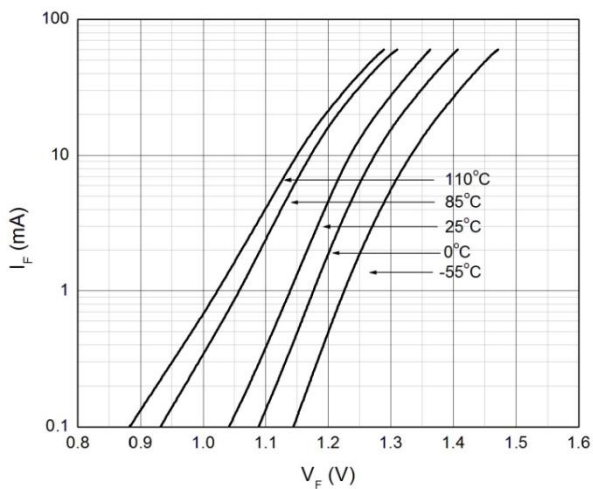


Fig.4 Collector Dark Current vs. Ambient Temperature

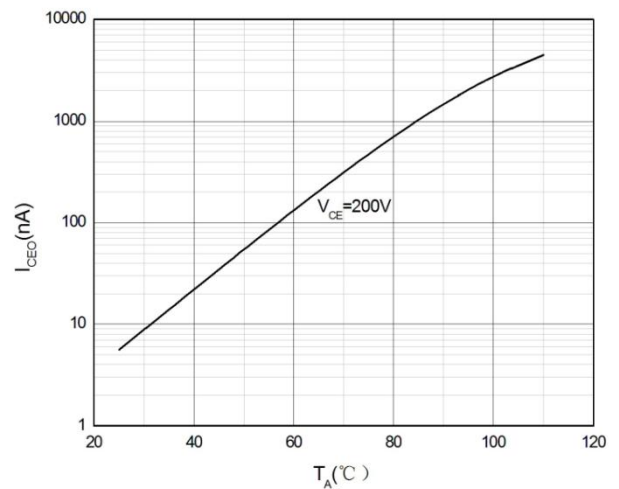
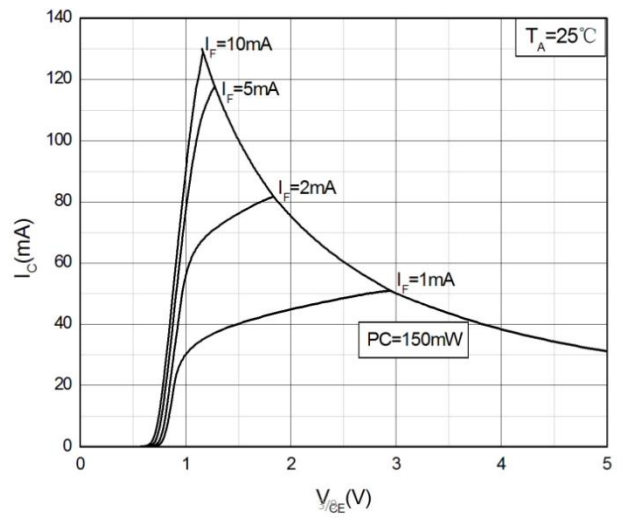
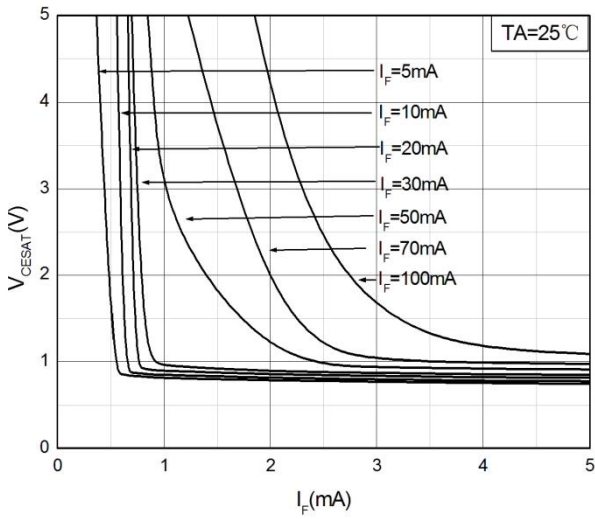


Fig.5 Collector-emitter Saturation Voltage vs. Forward Current

Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Normalized Current Transfer Ratio vs. Forward Current

Fig.8 Normalized Current Transfer Ratio vs. Ambient Temperature

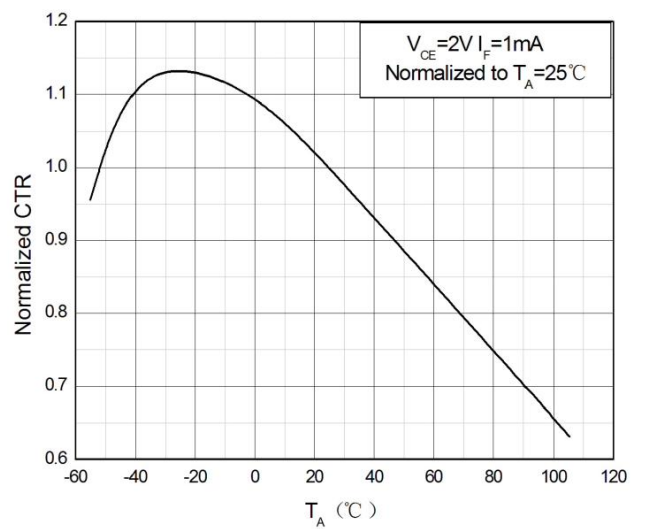
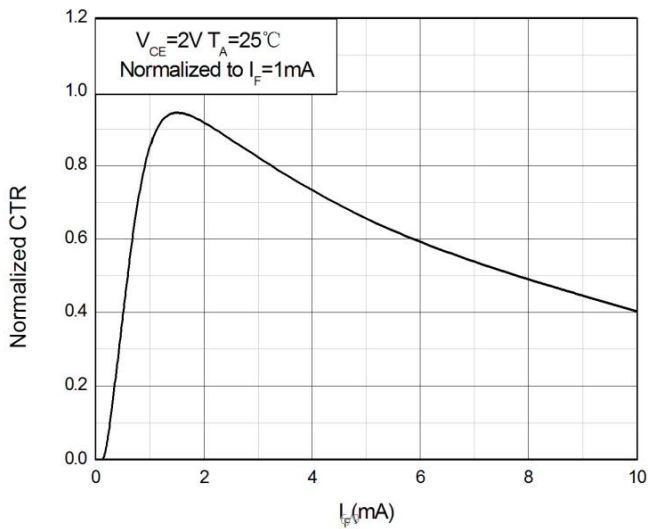


Fig.9 Collector-emitter Saturation Voltage vs. Ambient Temperature

Fig.10 Switching Time vs. Load Resistance

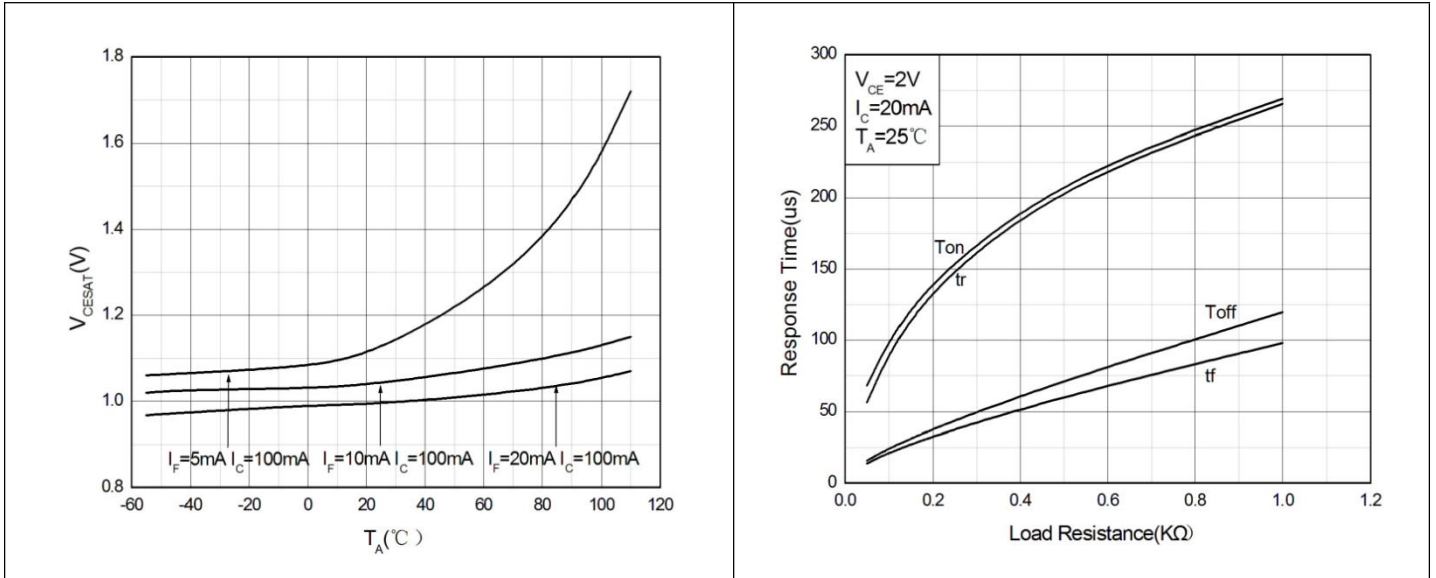
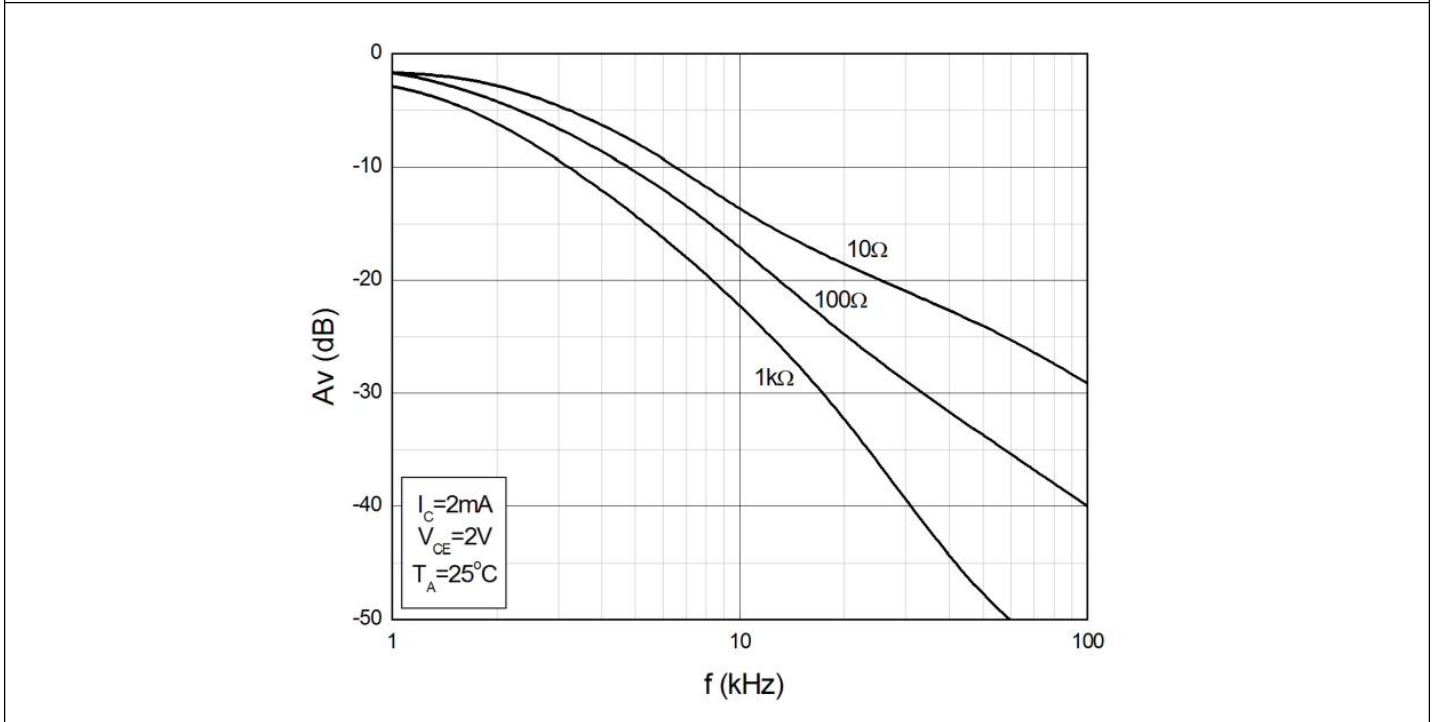


Fig.11 Frequency Response



TEST CIRCUITS

Fig.12 Test Circuits of Response Time

Fig.13 Curves of Response Time

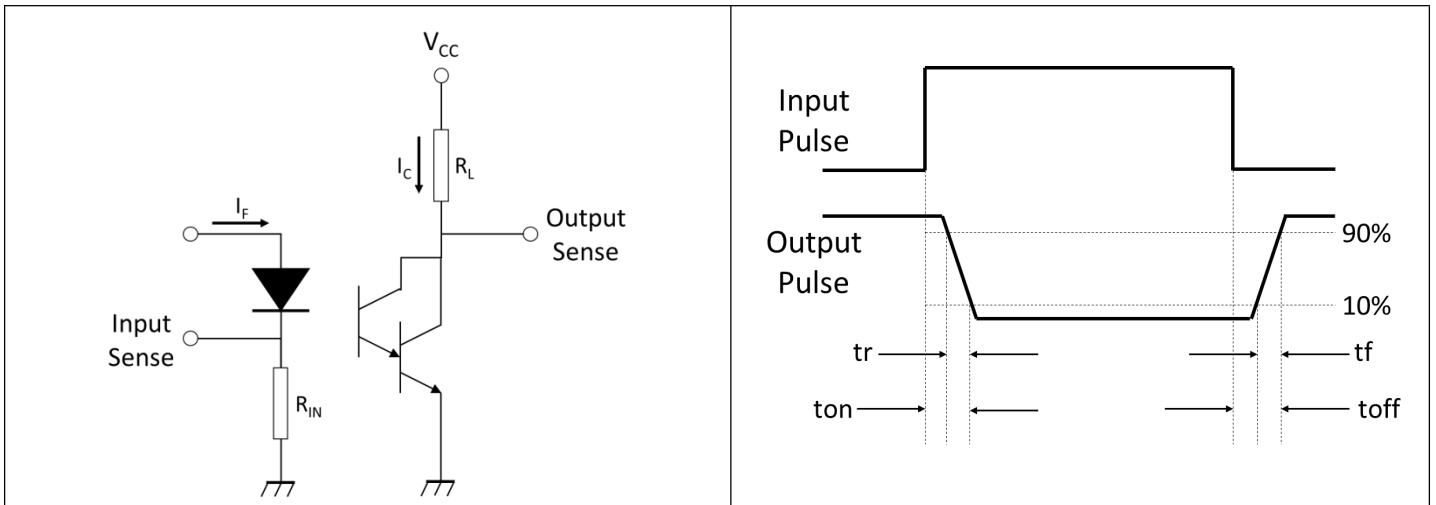
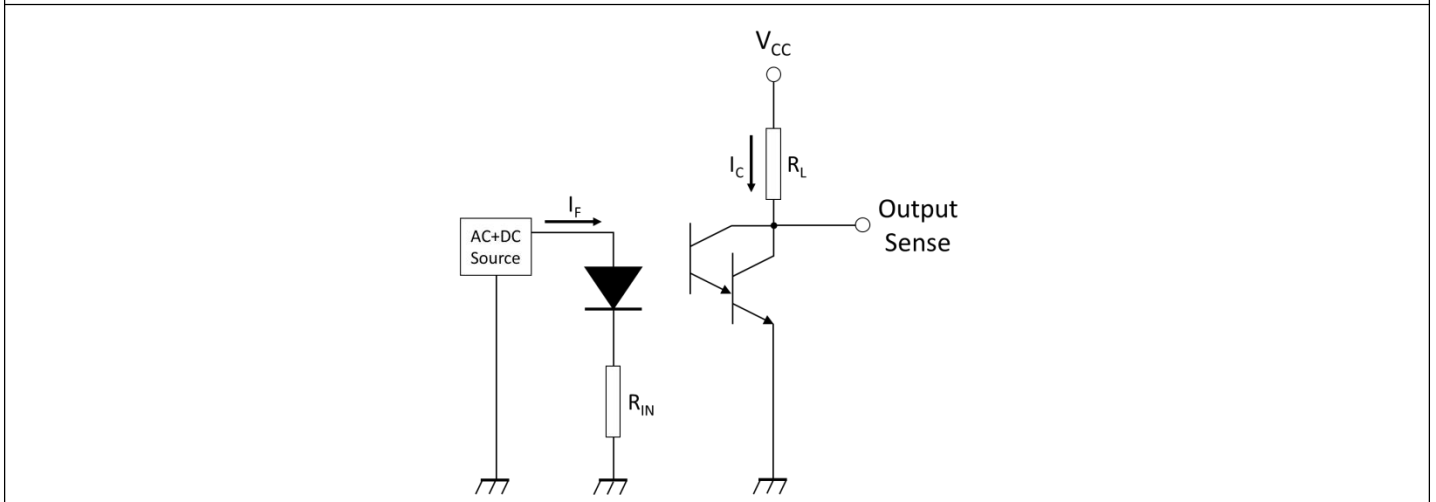
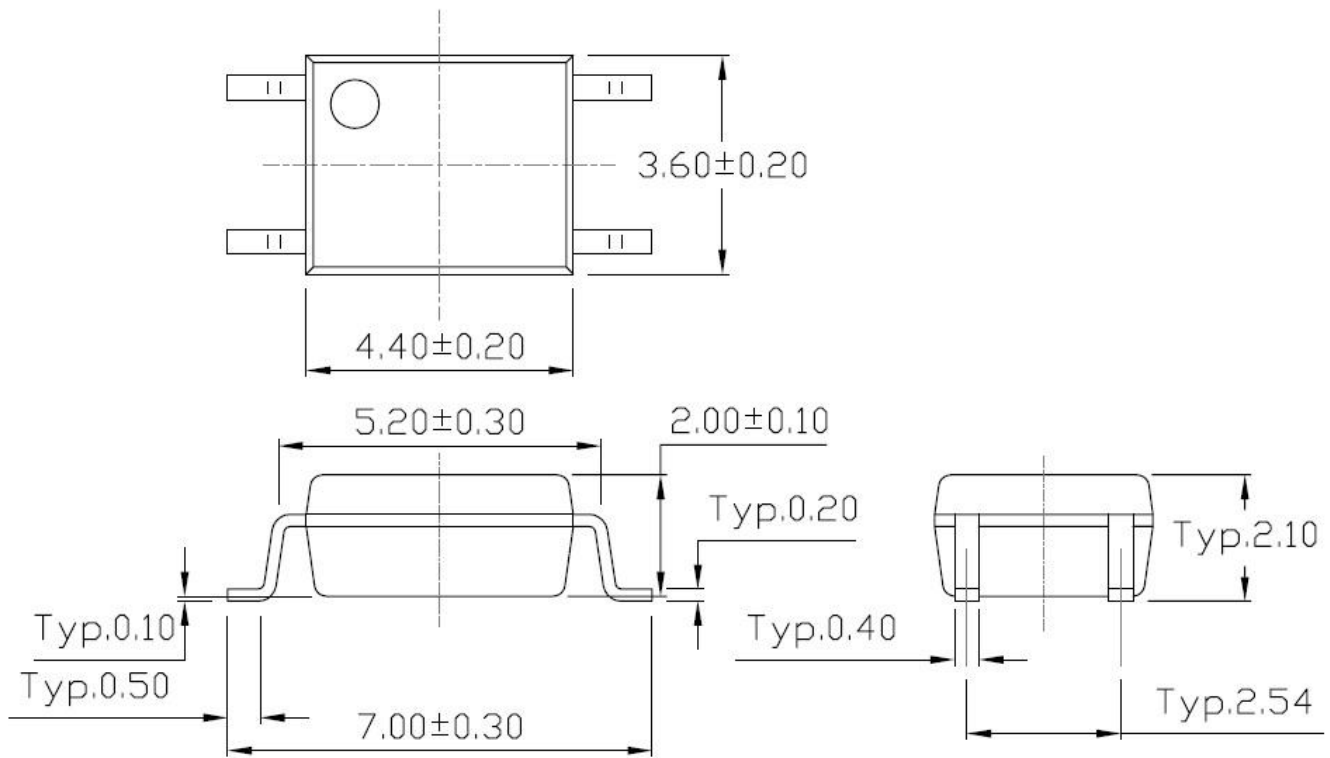


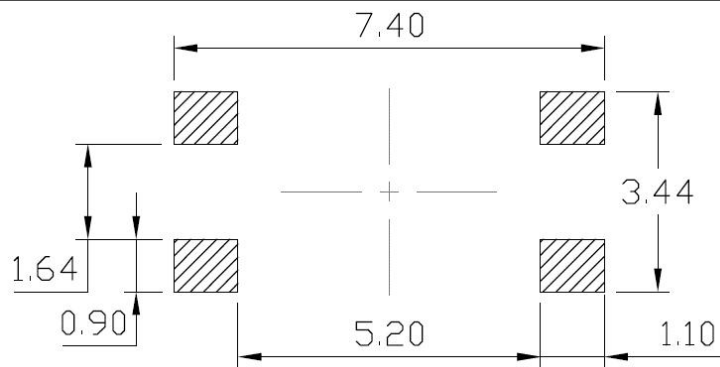
Fig.14 Test Circuits of Frequency Response



PACKAGE DIMENSIONS (Dimensions in mm unless otherwise stated)

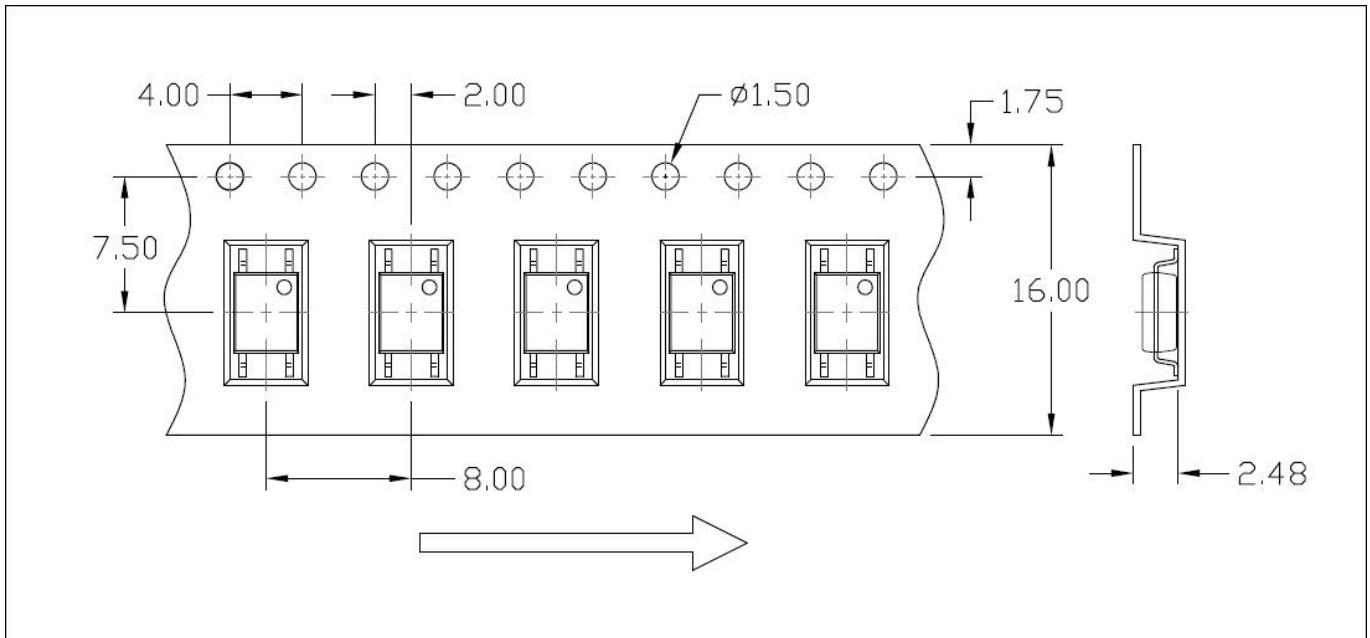


Recommended Solder Mask (Dimensions in mm unless otherwise stated)

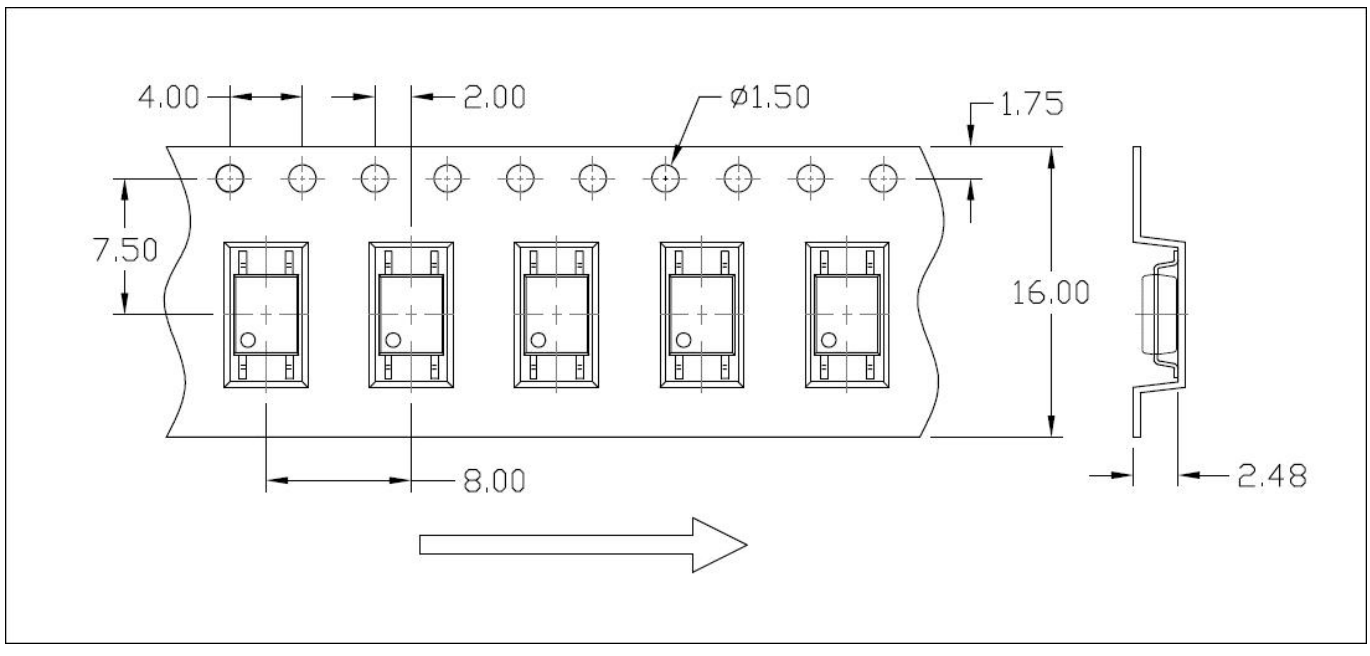


CARRIER TAPE SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option T1

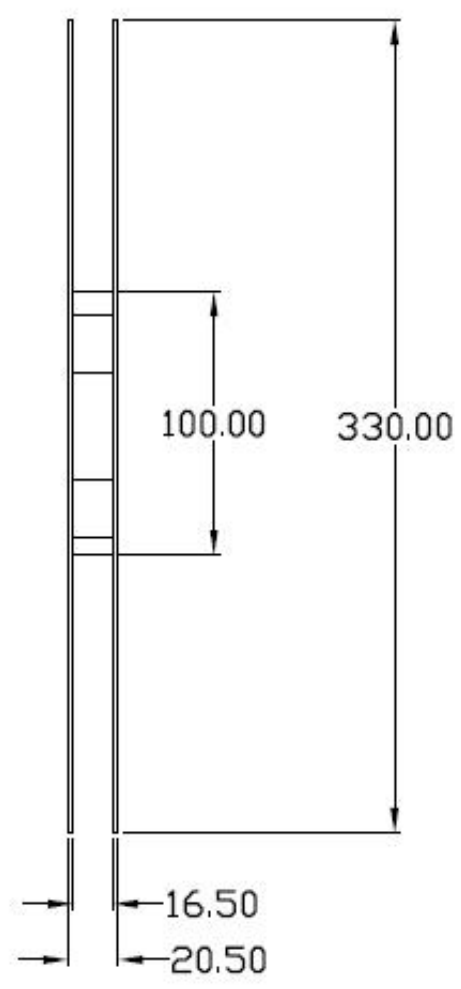
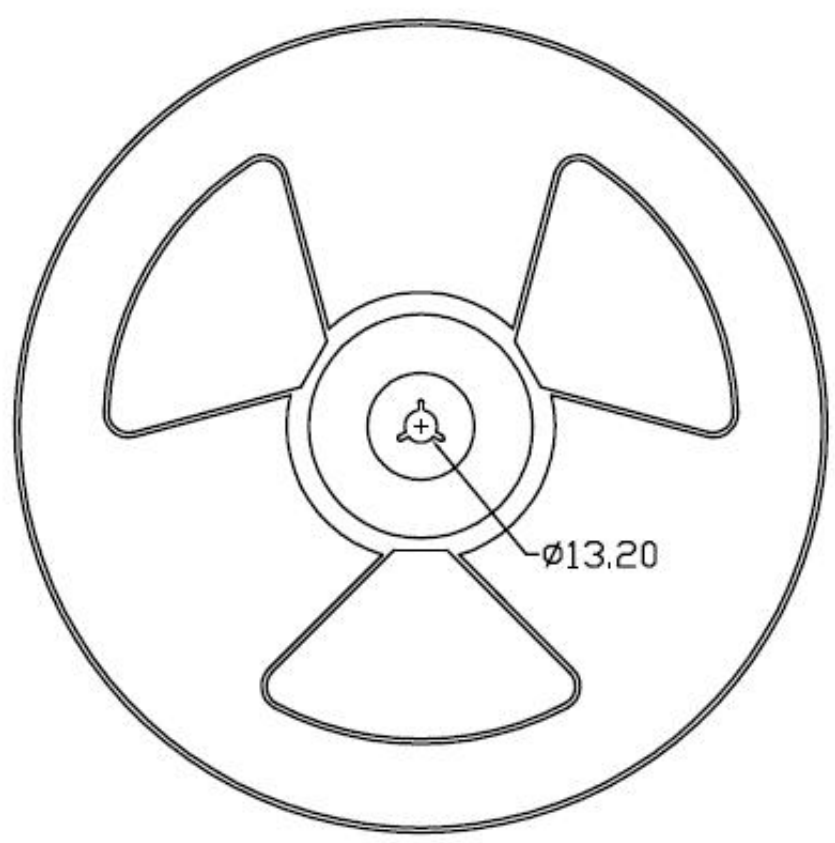


Option T2



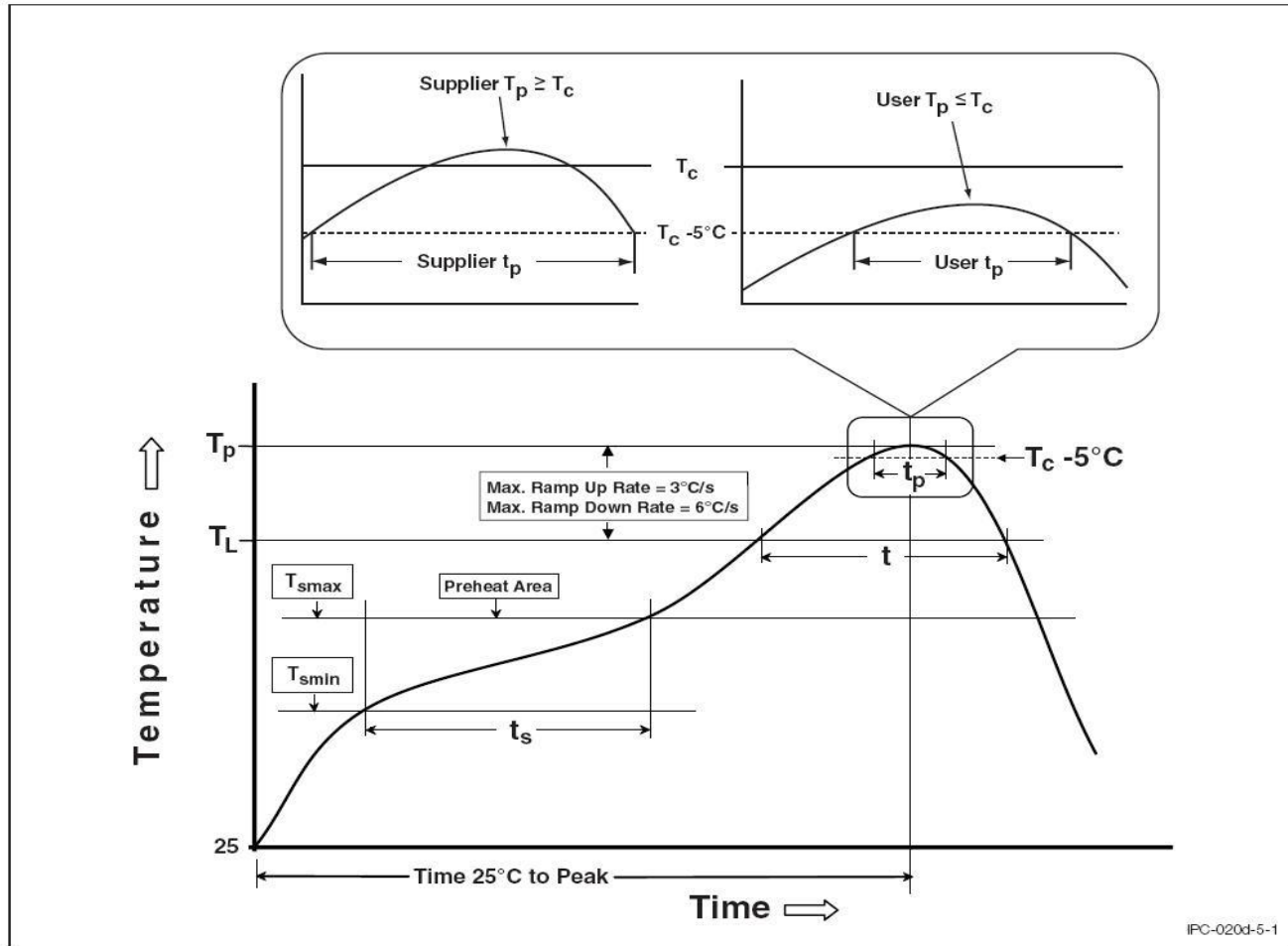
REEL SPECIFICATIONS (Dimensions in mm unless otherwise stated)

Option T1 & T2



REFLOW INFORMATION

REFLOW PROFILE



Profile Feature	Sn-Pb Assembly Profile	Pb-Free Assembly Profile
Temperature Min. (T_{smin})	100	150°C
Temperature Max. (T_{smax})	150	200°C
Time (t_s) from (T_{smin} to T_{smax})	60-120 seconds	60-120 seconds
Ramp-up Rate (t_L to t_P)	3°C/second max.	3°C/second max.
Liquidous Temperature (T_L)	183°C	217°C
Time (t_L) Maintained Above (T_L)	60 – 150 seconds	60 – 150 seconds
Peak Body Package Temperature	235°C +0°C / -5°C	260°C +0°C / -5°C
Time (t_P) within 5°C of 260°C	20 seconds	30 seconds
Ramp-down Rate (T_P to T_L)	6°C/second max	6°C/second max
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Transistor Output Optocouplers](#) category:

Click to view products by [SLKORMICRO](#) manufacturer:

Other Similar products are found below :

[LTV-814S-TA](#) [LTV-852S](#) [66095-001](#) [PS2561-1-A](#) [PS2561A-1-W-A](#) [PS2561L1-1-A](#) [PS2561L-1-V-A](#) [PS2706-1-A](#) [PS2815-1-A](#) [MRF658](#)
[ILD2-X006](#) [ILQ615-3X016](#) [LDA102S](#) [SFH615A-4XSM TR](#) [PS2561DL-1Y-F3-A](#) [PS2561L1-1-L-A](#) [PS2562-1-V-A](#) [PS2565L-1-A](#)
[PS2581L2-A](#) [PS2701A-1-F3-P-A](#) [PS2711-1-A](#) [PS2801-1-F3-P-A](#) [PS2833-4-A](#) [PS2841-4A-AX](#) [LTV-702FS](#) [LTV-702V](#) [LTV-702VB](#) [LTV-](#)
[816S-TA](#) [LTV-825S](#) [TCET2100](#) [TLP290-4\(E\(T](#) [IL215AT](#) [WPPC-A11066AA](#) [WPPC-A11066AD](#) [WPPC-A11084ASS](#) [WPPC-A21068AA](#)
[WPPC-D11066AA](#) [WPPC-D21068ED](#) [WPPC-D410616EA](#) [WPPC-D410616ED](#) [X4IAC24A](#) [4N26-X001](#) [EL1010\(TA\)-VG](#) [SFH600-2X007](#)
[TCMT1118](#) [VO206AT](#) [WPPC-D21068EA](#) [WPPC-D11064AD](#) [WPPC-A410616AD](#) [WPPC-A21068AD](#)